Picosecond Spin Current Generation from Vicinal Metal-Antiferromagnetic **Insulator Interfaces**

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We report the picosecond spin current generation from the interface between a heavy metal and a vicinal antiferromagnet insulator Cr_2O_3 by laser pulses at room temperature and zero magnetic field. It is converted into a detectable terahertz emission in the heavy metal via the inverse spin Hall effect. The vicinal interfaces are apparently the source of the picosecond spin current, as evidenced by the proportional terahertz signals to the vicinal angle. We attribute the origin of the spin current to the transient magnetic moment generated by an interfacial nonlinear magnetic-dipole difference-frequency generation. We propose a model based on the in-plane inversion symmetry breaking to quantitatively explain the terahertz intensity with respect to the angles of the laser polarization and the film azimuth. Our work opens new opportunities in antiferromagnetic and ultrafast spintronics by considering symmetry breaking.

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Antiferromagnets (AFMs) exhibit promising advantages and great potential in spintronic applications due to their unique properties, including ultrafast spin dynamics and zero (or negligible) magnetic moment. These characteristics make AFMs a promising platform for developing devices with ultrafast information processing speed, robustness against external magnetic field perturbations, and high density [1-7]. Spin currents play a crucial role in transporting and manipulating information in spintronic devices [8–13]. In the past few years, much research has focused on exploring static spin current generated from AFMs, such as the spin Seebeck effect (SSE) [14–16] and spin pumping [17–19]. These mechanisms are similar to those observed in ferromagnets. However, the requirement of a strong magnetic field in these effects severely impedes their exploitations and applications [6]. Moreover, the static spin currents generated from AFMs are not fundamentally different from those generated from ferromagnets.

Ultrafast spin currents are an essential ingredient for high-speed spintronic devices [6,7,20–25]. It is anticipated that AFMs can play to their strength of ultrafast spin dynamics on the picosecond timescale to produce picosecond spin currents. However, ferromagnets have been more used as the sources of the picosecond spin currents in two ways with femtosecond laser excitation: the spindependent superdiffusive transport of nonequilibrium hot electrons [21–27] and the picosecond SSE [20,28–32], although the spin dynamics of ferromagnets is on the nanosecond timescale [33–35]. In addition, the conversion

of picosecond spin currents from pulse electrical currents in a heavy metal (HM) via the spin Hall effect (SHE) has been demonstrated [36]. Until recently, two distinctive mechanisms for optically generated picosecond spin currents in AFMs are discovered in Pt/NiO bilayers. One is the stimulated Raman-induced collinear difference-frequency generation (DFG) optical process [6,37]. This process is permitted only when laser pulses propagate along the threefold symmetry axis of the single crystalline NiO film [38]. The other one is the spin-phonon interactions [7], where the laser-pulse-excited strain waves in Pt modulate the magnetic anisotropy of NiO, inducing Néel vector oscillations and exciting transient antiferromagnetic magnons. The presence of an out-of-plane Néel vector component is required for this mechanism. Additionally, the picosecond SSE has been demonstrated to generate ultrafast spin currents in HM/AFM bilayers with applying large magnetic field [39]. In all previous reports, the bulk properties of ferromagnets, HMs or AFMs have predominantly influenced the generation of picosecond spin currents and it needs to be specific crystal orientation or large magnetic field for AFMs.

The transient magnetic moment, accompanied by the change of the angular momentum over time, can generate a short pulse spin current [40]. Nonlinear magnetic-dipole (MD) transitions can be utilized as an optical method to excite transient magnetic moment in the terahertz (THz) frequency [6,38]. While nonlinear electric-dipole transitions at vicinal surfaces or interfaces have been intensively studied in nonlinear optics [41,42], it remains unexplored whether the nonlinear MD transition at vicinal metal-AFM interfaces can excite transient magnetic moments and resultant spin current due to the breaking of space- and time- inversion symmetry. In this work, we show the generation of picosecond spin currents using a femtosecond pulse laser in HM/Cr₂O₃ bilayers grown on a vicinal substrate at room temperature and zero magnetic field. The picosecond spin current is converted into a transient charge current in the HM layer via the inverse spin Hall effect (ISHE) [43], resulting in detectable electromagnetic emissions with THz frequencies. The intensity of the THz signal is found to be proportional to the vicinal angle and negligible for the flat film, manifesting that the picosecond spin current is solely contributed from the step edges. We propose an interfacial MD DFG to excite transient magnet moments or magnons as the origin of the picosecond spin current. This finding opens a new avenue for optically generating ultrafast spin current from interface states, in sharp contrast to the existing approaches primarily based on bulk properties.

We choose one-side-polished vicinal $Al_2O_3(0001)$ substrates with steps parallel to the $[10\overline{1}0]$ direction to epitaxially grow Cr₂O₃ films using pulsed laser deposition. The substrates were annealed at 1000 °C for 4 h in air to obtain stepped surfaces. Figure 1(a) shows a typical atomic force microscopy (AFM) image of an Al₂O₃(0001) substrate, clearly displaying the step morphology with straight step edges and uniformly flat terraces, the averaging \sim 54 nm in width. The height profile as marked by the white line in Fig. 1(a) shows that the step edges have an almost equal height of ~0.44 nm, corresponding to one-third of the lattice constant along the Al₂O₃ [0001] axis [44]. The estimated vicinal angle α of 0.5°, derived from the terrace width and step height, is consistent with the nominal value. Subsequently, the Cr_2O_3 films were grown at 700 °C in an oxygen atmosphere of 0.07 torr with a KrF excimer laser at a repetition of 4 Hz with an energy density of 50 mJ/mm^2 . The structure of the Cr₂O₃ films was characterized by in situ reflection high energy electron diffraction and x-ray diffraction (see Supplemental Material [45]). The surface displays cracks due to the lattice mismatch between Cr_2O_3 and Al_2O_3 [Fig. 1(b)], but it remains a steplike surface. The vicinal angle α of the film is estimated to be $\sim 0.5^{\circ}$ from the height profile [Fig. 1(b)], consistent with that of the substrate. The metallic films were directly deposited onto Cr₂O₃ using dc magnetron sputtering at ambient temperature.

Figure 1(c) illustrates the time-domain THz measurement configuration to demonstrate the laser-stimulated picosecond spin currents. A linearly polarized femtosecond laser with temporal duration 290 fs, central wavelength 1030 nm, and repetition rate 50 kHz (Pharos, Light Conversion) is perpendicularly incident to the sample surface. The direction of the laser polarization and the



FIG. 1. AFM image and height profile marked by the white line of (a) Al₂O₃(0001) substrate and (b) 15-nm-thick Cr₂O₃(0001) film with $\alpha = 0.5^{\circ}$. (c) The schematic of the time-domain THz spectroscopy measurement setup. (d) The relation between crystal and laboratory coordinates. The polarization of the laser E_{laser} is defined by the angle θ with respect to x'. The sample surface is set in the x'y' plane and the azimuth angle is defined by φ with respect to x'.

step direction are defined by the angle θ and φ , respectively, with respect to the x' axis of the laboratory coordinates, as shown in Figs. 1(c) and 1(d). A transient spin current excited by the laser pulses flows into the HM layer and is then converted into a transient transverse charge current via ISHE. This charge current generates an electromagnetic wave with THz frequencies. To detect the THz signal, we employ standard electro-optical sampling using a 1-mmthick GaP crystal in a dry N₂ environment. The emitted THz waveforms are found to be linearly polarized (see Supplemental Material [45]). In the following measurements, the polarization direction of a wire-grid polarizer placed in front of the GaP crystal is fixed along the x' axis to analyze the x' component of the THz electrical field $E_{x'}^{\text{THz}}$. All THz measurements were performed at room temperature.

Figure 2(a) shows the temporal evolution of $E_{x'}^{\text{THz}}$ measured on a series of Pt(4)/Cr₂O₃(15) bilayers grown on Al₂O₃(0001) substrates with different α under a laser pump fluence $P = 2.2 \text{ mJ/cm}^2$ at $\theta = \varphi = 0^\circ$, where the values in parentheses are the thickness in nanometers. The THz emission amplitude is negligible for the sample with $\alpha = 0.1^\circ$, but it rapidly increases with increasing α . The dependence of the peak values, extracted from Fig. 2(a), on α is plotted in Fig. 2(b). The peak values of $E_{x'}^{\text{THz}}$ are linearly dependent on α and approaches zero at $\alpha = 0^\circ$, highlighting the decisive role of the vicinal surface in THz generation. These observations immediately exclude the mechanism discovered in Pt/NiO(111) bilayers where the films are grown on flat substrates [6]. We compare the THz



FIG. 2. (a) The time domain spectroscopy of $E_{x'}^{\text{THz}}$ measured on a series of Pt(4)/Cr₂O₃(15) bilayers grown on the Al₂O₃(0001) substrates with different α at $\theta = \varphi = 0^{\circ}$. (b) The α dependence of the peak values of $E_{x'}^{\text{THz}}$.

emission of Pt/Cr₂O₃ with those of Pt/NiO, Pt/Y₃Fe₅O₁₂, and Pt/Py (see Supplemental Material [45]). The amplitude is comparable with those of Pt/NiO and Pt/Y₃Fe₅O₁₂, but much smaller than that of Pt/Py. The bandwidths of these samples are nearly the same. It is plausibly limited by the time duration of the laser as used in generating and detecting the THz emission, which is the common feature in these measurements. The THz signals of Pt/Cr₂O₃ are significantly stronger than those of the samples grown on the unannealed substrates with rougher surfaces (see Supplemental Material [45]), again indicating an interfacial origin.

To investigate the origin of the THz emission, we performed several control experiments. First, we fabricated three control samples, $Al(5)/Cr_2O_3(15)$ bilayer, Pt(4)single layer, and single $Cr_2O_3(15)$ film, on vicinal Al₂O₃ substrates with $\alpha = 2^{\circ}$ to carry out the same measurements. No THz signal is detected in any of the control samples, as shown in Fig. 3(a), where either the Pt or Cr₂O₃ layer is absent. This result highlights the importance of Pt and Cr₂O₃ and excludes the possibility of emission from the Cr₂O₃ layer itself due to the nonlinear optical effects. Second, the THz waveform changes the polarity when W is replaced with Pt on Cr_2O_3 [Fig. 3(a)], indicating the opposite direction of the transient charge current for the W and Pt samples. Considering that W and Pt have opposite spin Hall angles [54], this observation is consistent with the spin current scenario. Furthermore, when considering the negligible THz signal in the Al/Cr_2O_3 sample, where Al has a very small spin Hall angle [55], we can unambiguously conclude the THz emission arising from the picosecond spin current. Third, the absence of signal in the single Pt film further confirms that our observation is related to antiferromagnet and hence spin current.

Next, we investigated the mechanism of the picosecond spin current generation. Cr_2O_3 is a magnetoelectric AFM material with a corundum type crystal structure, and a bulk Néel temperature of 307.5 K [47,56]. The Néel temperature of our films is measured to be ~360 K, consistent with previous report (see Supplemental Material [45]). The



FIG. 3. (a) $E_{x'}^{\text{THz}}$ of Al(5)/Cr₂O₃(15), Pt(4), Cr₂O₃(15), Pt(4)/Cr₂O₃(15), and W(4)/Cr₂O₃(15) on Al₂O₃ substrates with $\alpha = 2^{\circ}$ at $\theta = \varphi = 0^{\circ}$. (b) Response of $E_{x'}^{\text{THz}}$ to external fields of Pt(4)/Cr₂O₃(15) with $\alpha = 2^{\circ}$ at $\theta = \varphi = 0^{\circ}$. (c) The time domain spectroscopy of $E_{x'}^{\text{THz}}$ measured on Pt(4)/Cr₂O₃(15) with different pump laser fluence with $\alpha = 2^{\circ}$ at $\theta = \varphi = 0^{\circ}$. (d) The peak values of $E_{x'}^{\text{THz}}$ as a function of the pump fluence, the solid blue line is a linear fit.

temperature of Cr_2O_3 is estimated to increase ~3 K due to the laser heating by a numerical simulation, below the Néel temperature (see Supplemental Material [45]). The Néel vector is along the [0001] direction, perpendicular to the film plane. An uncompensated magnetic moment at the boundary (surface or interface) is present regardless of roughness due to a general symmetry argument [56,57]. This uncompensated magnetic moment could be the source of the picosecond spin current, similar to what is observed in HM/FM bilayers. First, we found that the signals remain almost unchanged when the polarity of an in-plane 1000-Oe external magnetic field is reversed [Fig. 3(b)], inconsistent with the THz signal generated from a ferromagnet. Second, considering that the uncompensated magnetic moment in Cr_2O_3 (0001) is perpendicular to the surface, the THz emission would not be expected from ISHE even if a spin current is excited. Therefore, we can rule out this possibility.

In the optical process, a magnetic moment $\mathbf{M}(\Omega)$ at frequency Ω could be excited through the MD transition even for an AFM without applying a magnetic field:

$$\mathbf{M}(\Omega) \propto \chi^{(1)\mathrm{MD}} \mathbf{E}(\Omega) + \chi^{(2)\mathrm{MD}} : \mathbf{E}(\Omega - \omega) \mathbf{E}(\omega) + \cdots, \quad (1)$$

where $\mathbf{E}(\Omega - \omega)$ and $\mathbf{E}(\omega)$ are the electric fields of the light wave at frequency $\Omega - \omega$ and ω , respectively [58]. The first term on the right-hand side corresponds to the linear magnetoelectric effect with the corresponding linear susceptibility $\chi^{(1)\text{MD}}$. The second term describes the generation of a magnetic moment through a MD DFG process

with the corresponding nonlinear susceptibility $\chi^{(2)\text{MD}}$, which is a third-rank axial tensor. This induced **M** could lead to a picosecond SSE owing to the laser pulse excited temperature gradient ∇T , which is proportional to *P* [29]. According to the SSE mechanism, $E_{\nu'}^{\text{THz}}$ is determined by

$$E_{x'}^{\text{THz}} \propto J_s \propto \nabla TM \propto PM, \qquad (2)$$

where J_s is the amplitude of the spin current. Figure 3(c) presents $E_{x'}^{\text{THz}}$ measured with different *P* on Pt(4)/Cr₂O₃(15) at $\theta = \varphi = 0^{\circ}$ and $\alpha = 2^{\circ}$. The peak signals are proportional to *P*, as shown in Fig. 3(d). It means that **M** is independent of *P* according to Eq. (2), contrary to Eq. (1) that **M** is correlated with *P* or **E**. Therefore, the SSE mechanism can be excluded to explain our observations.

Owing to the conservation of angular momentum, the variation of **M** and its associated angular momentum over time can produce a spin current in the adjacent normal metal, similar to the spin pumping effect. Therefore, the picosecond impulse **M** itself can generate the picosecond spin current with its amplitude proportional to **M**, $M \propto J_s$. Given that $J_s \propto E_{x'}^{\text{THz}} \propto P \propto E^2$ [Fig. 3(d)], we infer that the impulse **M** arises solely from the second term of Eq. (1).

The impulse M and the resulting THz emission can originate from various sources, including the bulk, terraces, and step edges on vicinal interface. Since the bulk properties and the area of the terraces are irrelevant to α , one would expect that the THz emission is independent of α . The negligible THz signal for $\alpha \sim 0^{\circ}$ [Fig. 2(b)] provides evidence that the contributions from the bulk and the terraces can be omitted. On the other hand, due to the in-plane inversion symmetry breaking at the steps, photons are in a local asymmetric potential field around the step edges. As a result, the nonlinear MD transition occurs only around the step edges [58], meaning that M is localized around the step edges and the magnitude is proportional to the step height. If the direction of the steps is reversed, the direction of **M** is reversed. Therefore, the total **M**, which is the integral of all moments at the step edges, is approximately proportional to α or the total step height, consistent with the behavior of $E_{x'}^{\text{THz}}$, regardless of the cracks in the films [Fig. 1(b)].

The MD transition contributed from $\chi^{(2)MD}$ can be classified into time-symmetric (*i*-type) $\chi^{(i)}$ and timeantisymmetric (*c*-type) $\chi^{(c)}$ susceptibilities for magnetic materials [59,60], $\chi^{(2)MD} = \chi^{(i)} + \chi^{(c)}$. The direction of the magnetic moment is reversed by time inversion, which is equivalent to the switching of the antiferromagnetic Néel vector. In our as-grown Cr₂O₃(0001) films, there are randomly distributed opposite 180° antiferromagnetic domains with $\chi^{(i)}$ of the same sign and $\chi^{(c)}$ of the opposite sign. The THz signals coming from each domain are coherently superposed, resulting in the cancellation of the contribution from $\chi^{(c)}$ and leaving only the contribution from $\chi^{(i)}$.

The magnetic point group of the vicinal Cr_2O_3 surface below the Néel temperature is \underline{m} , which consists of two symmetry operators, 1 and $\underline{\hat{Z}}_y$ [60]. Here, we use crystal coordinates to describe the components of the susceptibility tensor, as depicted in Fig. 1(d), in which the *y* axis is along the step edge and the *x* axis is perpendicular to the step face. For light propagating along the *z* axis and ISHE in the HM layer depending only on the in-plane magnetic moment \mathbf{M}_{x-y} , only three independent nonzero components need to be considered for $\chi^{(i)}$, $\chi^{(i)}_{yxx}$, $\chi^{(i)}_{yyy}$ and $\chi^{(i)}_{xxy} = \chi^{(i)}_{xyx} \equiv \gamma$. The excited \mathbf{M}_{x-y} is then given by

$$\mathbf{M}_{x-y} = \begin{pmatrix} M_x \\ M_y \end{pmatrix} \propto \alpha \begin{pmatrix} 2\gamma E_x E_y \\ \chi_{yxx}^{(i)} E_x^2 + \chi_{yyy}^{(i)} E_y^2 \end{pmatrix}, \quad (3)$$

where it is applied that \mathbf{M}_{x-y} has a linear dependence on α for small α . In our experimental configuration and the laboratory coordinate system, one can calculate the y' component of \mathbf{M} , $M_{y'}$, to obtain the THz emission for the laser polarization along the x' axis, i.e., $\theta = 0^{\circ}$,

$$E_{x'}^{\text{THz}} \propto M_{y'} \propto [(\chi_{yyy}^{(i)} - 2\gamma)\sin^2\varphi + \chi_{yxx}^{(i)}\cos^2\varphi]\alpha P\cos\varphi.$$
(4)

When the laser polarization is varied while fixing the sample orientation with $\varphi = 0^{\circ}$, the THz emission is calculated as

$$E_{x'}^{\text{THz}} \propto M_{y'} \propto [\chi_{yxx}^{(i)} + (\chi_{yyy}^{(i)} - \chi_{yxx}^{(i)})\sin^2\theta]\alpha P.$$
 (5)

According to Eqs. (4) and (5), the amplitude of the THz emission is proportional to α and *P*, in good agreement with the experimental results [Figs. 2(b) and 3(d)].

To further validate the above phenomenological model based on symmetrical analysis, we performed angulardependent measurements. In Figs. 4(a) and 4(c), we present the THz waveforms of the $Pt(4)/Cr_2O_3(15)$ bilayers sample with $\alpha = 2^{\circ}$ for various φ at $\theta = 0^{\circ}$ and various θ at $\varphi = 0^{\circ}$, respectively. The corresponding $E_{x'}^{\text{THz}}$ peak values as functions of φ and θ are shown in Figs. 4(b) and 4(d), respectively. These angular dependences could be caused by the change of the laser absorption [61-63]. We find that the laser absorption is independent of θ and hence this impact is excluded (see Supplemental Material [45]). We fitted the data for φ - and θ -scans with Eqs. (4) and (5), respectively. The fittings are in good agreement with the data and yield $\chi_{yxx}^{(i)}:\chi_{yyy}^{(i)}:\chi_{xxy}^{(i)}:\chi_{xyx}^{(i)}\approx 55:35:-12:-12.$ Without considering the symmetry of the Cr₂O₃ lattice, the mirror symmetry is broken about the yz pane due to the steps, but it remains about the xz pane in the vicinal surface. Therefore, the second-order nonlinear optical process should be strongest at the light polarization parallel to the



FIG. 4. The THz waveforms of the $Pt(4)/Cr_2O_3(15)$ bilayers with $\alpha = 2^\circ$ for (a) various φ at $\theta = 0$ and (c) various θ at $\varphi = 0^\circ$. The corresponding peak values of $E_{x'}^{THz}$ as functions of (b) φ and (d) θ . The red dots are the raw data, and the blue lines represent the fitted curves with Eqs. (4) and (5), respectively.

x axis [41]. This is consistent with the strongest signal at $\varphi = 0^{\circ}$ and 180° in Fig. 4(b) and at $\theta = 0^{\circ}$ and 180° in Fig. 4(d). Note that rotating the sample by 180° is equivalent to changing the sign of α , resulting the sign reversal of $E_{x'}^{\text{THz}}$. As a result, the THz emission amplitude exhibits an oscillation period of 360° in the φ scan but an oscillation period of 180° in the θ scan. In the φ scan, the threefold symmetry of Cr₂O₃ is not present, again confirming the negligible bulk contribution.

In summary, we show a transient magnetic moment optically excited at the vicinal metal-Cr₂O₃ interface at zero magnetic field and room temperature. This transient magnetic moment is converted into a picosecond spin current. We attribute these observations to the interfacial MD DFG process induced magnetic moment, which originates from the in-plane inversion symmetry breaking at interface. This effect disappears in the flat sample, confirming the sole contribution from the step edges. We observe a clear dependence on laser polarization direction and sample azimuth angle, which is consistent with our theoretical model based on symmetry analysis. Our findings highlight that the MD DFG process can be a general approach to generate ultrafast spin current by considering the symmetries. Our observation is understood by the nonlinear optical process due to the spaceand the time-inversion symmetry breaking at the vicinal interfaces. We anticipate that the picosecond spin current generation by this interfacial effect is valid for other HM-AFM or even HM-ferromagnet interfaces. This will open up more opportunities in antiferromagnetic and ultrafast spintronics.

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